ABSTRACT

METHOD OF FABRICATING IMPROVED CAPACITORS WITH PINHOLE REPAIR CONSIDERATION WHEN OXIDE CONDUCTORS ARE USED

A method of fabricating a metal-oxide-metal (MOM) capacitor, comprising the following steps. A bottom metal layer is deposited. A high dielectric constant oxide insulator is deposited layer over the bottom metal layer. The structure is annealed in an oxidizing ambient to cause the exposed bottom metal to form a metal oxide partially filling the one or more pin hole defects to repair those pin hole defects. An upper oxide conductor layer is then deposited over the high dielectric constant oxide insulator layer. An upper metal layer is deposited over said upper oxide conductor layer.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)